

S/N 08/903,486

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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al.

Examiner: W. Mintel

Serial No.: 08/903,486

Group Art Unit: 280

Filed: July 29, 1997

Docket: 303.326US1

Title: SILICON CARBIDE GATE TRANSISTOR

AMENDMENT AND RESPONSE

Assistant Commissioner for Patents

Washington, D.C. 20231

Applicant has reviewed the Office Action mailed January 18, 2000. Please amend the application as follows:

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IN THE SPECIFICATION

APR 26 2000
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Please amend the specification as follows:

C/1
On page 4, line 15, before FIG. 2 please insert --FIG. 1A is a cross-sectional view, illustrating generally one embodiment of a transistor according to one aspect of the invention, including a silicon carbide (SiC) gate and a semiconductor surface layer formed on an underlying insulating portion.--

C/2
On page 9, line 1, before FIG. 2 please insert the following paragraph: --FIG. 1A is a cross-sectional view illustrating generally, by way of example, another embodiment of an n-channel FET 128 provided by the invention. A source region 102 and a drain region 104 are formed in a thin semiconductor surface layer 130 that is formed on an underlying insulating portion 132. The other elements of the FET 128 are similar to the corresponding elements in the n-channel FET shown in FIG. 1, and have retained the same reference numerals for purposes of brevity.

IN THE DRAWINGS

OK
W/M
Please add Figure 1A to the drawings. A copy of Figure 1A is attached hereto. No new matter has been added.

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03 FC:102 234.00 0P

00000148 190743
00000148 144.00
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